



# **isc Silicon NPN Power Transistors**

#### **DESCRIPTION**

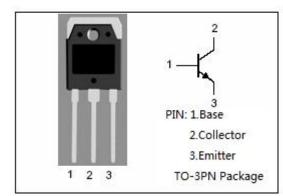
- Low Collector Saturation Voltage
   : V<sub>CE(sat)</sub>= 0.4V(Max)@ I<sub>C</sub>= 6A
- · Wide Area of Safe Operation
- Complement to Type 2SB922L
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

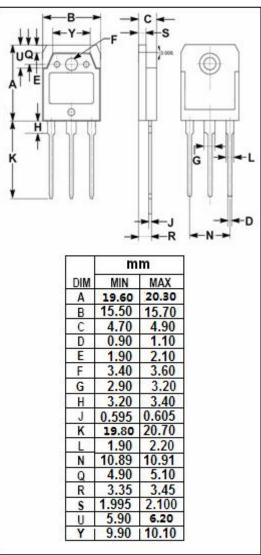
### **APPLICATIONS**

 Designed for relay drivers, high-speed inverters, converters, and other general high-current switching applications

## ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	90	V
V <sub>CEO</sub>	Collector-Emitter Voltage	80	V
V <sub>EBO</sub>	Emitter-Base Voltage	6	V
Ic	Collector Current-Continuous	12	А
I <sub>CP</sub>	Collector Current-Pulse	20	А
Pc	Collector Power Dissipation @ T <sub>C</sub> =25℃	80	W
TJ	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature Range	-55~150	$^{\circ}$







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2SD1238L

#### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 1mA ; R <sub>BE</sub> = ∞	80			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 1mA ; I <sub>E</sub> = 0	90			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 1mA ; I <sub>C</sub> = 0	6			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 6A; I <sub>B</sub> = 0.6A			0.4	V
Ісво	Collector Cutoff Current	V <sub>CB</sub> = 80V; I <sub>E</sub> = 0			100	μА
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 4V; I <sub>C</sub> =0			100	μА
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 2V	70		280	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 6A ; V <sub>CE</sub> = 2V	30			
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V		20		MHz
Switching times						
ton	Turn-on Time			0.2		μs
t <sub>stg</sub>	Storage Time	I <sub>C</sub> = 5A; I <sub>B1</sub> = I <sub>B2</sub> = 0.5A R <sub>L</sub> = 10 Ω; P <sub>W</sub> =20 μ s; V <sub>CC</sub> = 50V		1.7		μs
t <sub>f</sub>	Fall Time			0.2		μ <b>s</b>

## ♦ h<sub>FE-1</sub> Classifications

Q	R	S
70-140	100-200	140-280

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